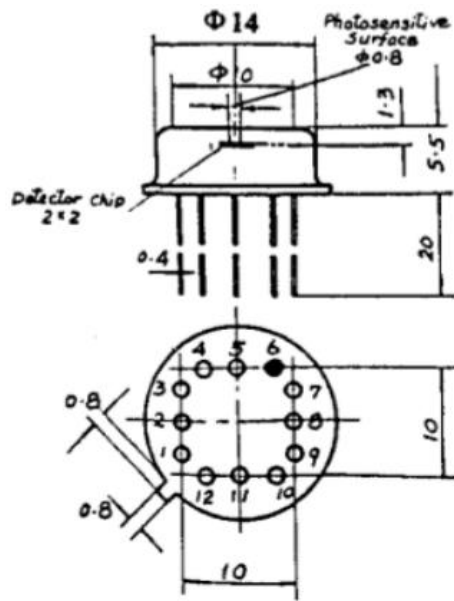


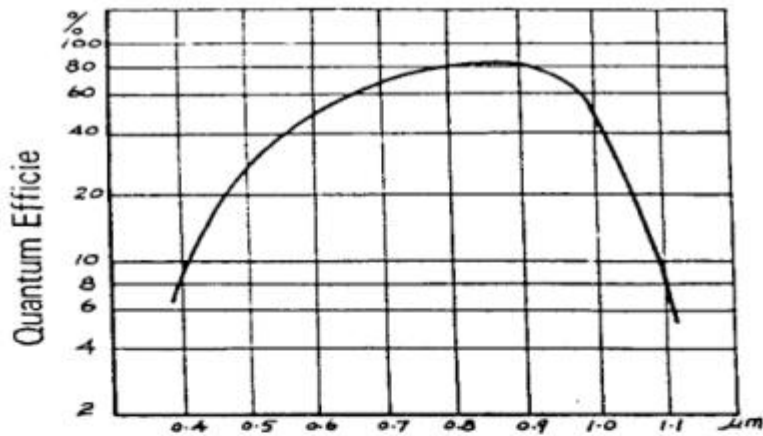
Parameter		Symbol	Unit	Numerical Value			
				Min	Typical	Max.	
1	Photosurface	Diam	Φ	mm		0.8	
		Area	A	mm ²		0.5	
2	Spectral Range			nm	400		1100
3	Dark Current		I_d	nA			200
4	Working Voltage		V_{opt}	V	275		425
5	Operating voltage temperature coefficient		K	V/°C	1.0		2.4
6	Voltage Response	1064nm	R_v	V/W × 10 ⁵	1.1	2.4	
		900nm	R_v	V/W × 10 ⁵	4.9	5.6	
7	Noise equivalent power	1064nm	NEP	PW/Hz ^{1/2}		0.11	0.27
		900nm	NEP	PW/Hz ^{1/2}		0.027	0.06
8	Response rise time		T_r	ns		8	10
9	Response fall time		T_f	ns		8	10
10	Output Impedance			Ω		25	50
11	Linear Output Voltage			V		0.7	
12	Output Voltage			V			2.0
13	Output terminal bias voltage			V	0.0	-0.7	-1.0
14	Amplifier supply voltage		V_s	V	±5.5	±6.0	±9.0
15	Amplifier supply current		I_s	mA		5	8
16	Operating Temperature		T_a	°C	-40		+70
17	Maximum reverse dark current		I_D	μ A			0.2
	Maximum photocurrent	average	I_P	mA			2.5
		Peak	I_P	mA			10



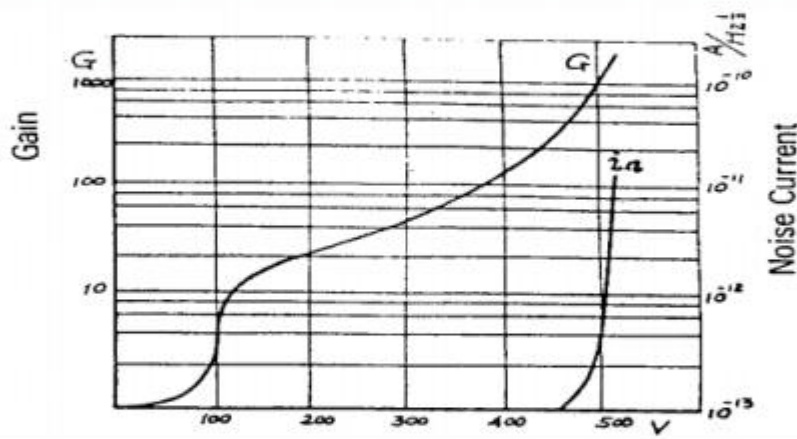
Construction and dimensions

Pin	Join Methods
1	Signal Output
2	—
3	Input Power: 6~-9V
4	APD bias voltage
5	—
6	Pipe shell earthing
7	Load earthing
8	temperature compensation AD509:anode
9	temperature compensation AD509:cathode
10	Input Power earthing
11	—
12	Input Power: +6~-+9V

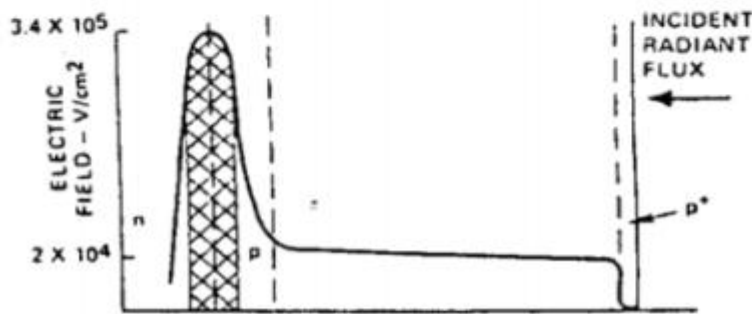
Pin Join Methods



Spectral response curve



$G \sim V_{\text{opt}}$, $I_n \sim V_{\text{opt}}$ curve



electric-field distribution